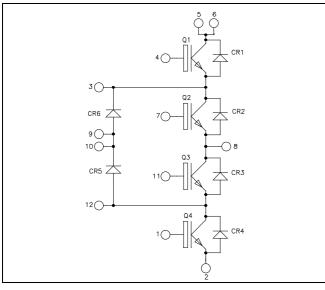
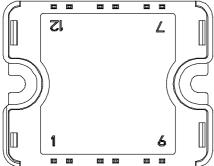


# Three level inverter Trench + Field Stop IGBT3 Power Module







All multiple inputs and outputs must be shorted together 5/6; 9/10

## Application

- Solar converter
- Uninterruptible Power Supplies

#### **Features**

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Very low stray inductance
- High level of integration

#### **Benefits**

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

### O1 to O4 Absolute maximum ratings

| VI to VI Insolute maximum ratings |                                       |                                  |            |   |  |  |  |  |  |
|-----------------------------------|---------------------------------------|----------------------------------|------------|---|--|--|--|--|--|
| Symbol                            | Parameter                             | Max ratings                      | Unit       |   |  |  |  |  |  |
| $V_{CES}$                         | Collector - Emitter Breakdown Voltage |                                  | 600        | V |  |  |  |  |  |
| т                                 | Continuous Collector Current          | $T_C = 25^{\circ}C$              | 32         |   |  |  |  |  |  |
| $I_{C}$                           | Continuous Conector Current           | $T_C = 80$ °C                    | 20         | Α |  |  |  |  |  |
| $I_{CM}$                          | Pulsed Collector Current              | $T_C = 25^{\circ}C$              | 40         |   |  |  |  |  |  |
| $V_{GE}$                          | Gate – Emitter Voltage                |                                  | ±20        | V |  |  |  |  |  |
| $P_{D}$                           | Maximum Power Dissipation             | $T_C = 25^{\circ}C$              | 62         | W |  |  |  |  |  |
| RBSOA                             | Reverse Bias Safe Operating Area      | $T_{\rm J} = 150^{\circ}{\rm C}$ | 40A @ 550V |   |  |  |  |  |  |

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



## All ratings @ $T_j = 25$ °C unless otherwise specified

## **Q1 to Q4 Electrical Characteristics**

| Symbol        | Characteristic                       | Test Conditions                    |                        | Min | Тур | Max | Unit |
|---------------|--------------------------------------|------------------------------------|------------------------|-----|-----|-----|------|
| $I_{CES}$     | Zero Gate Voltage Collector Current  | $V_{GE} = 0V, V_{CE} = 600V$       |                        |     |     | 250 | μΑ   |
| V             | Collector Emitter Saturation Voltage | , GE 10,                           | $T_j = 25$ °C          |     | 1.5 | 1.9 | V    |
| $V_{CE(sat)}$ |                                      |                                    | $T_{j} = 150^{\circ}C$ |     | 1.7 |     | ·    |
| $V_{GE(th)}$  | Gate Threshold Voltage               | $V_{GE} = V_{CE}, I_C = 300 \mu A$ |                        | 5.0 | 5.8 | 6.5 | V    |
| $I_{GES}$     | Gate – Emitter Leakage Current       | $V_{GE} = 20V, V_{CE} = 0V$        |                        |     |     | 300 | nA   |

## Q1 to Q4 Dynamic Characteristics

| Symbol           | Characteristic                      | Test Conditions  |  | Min | Typ  | Max  | Unit |
|------------------|-------------------------------------|--|--|-----|------|------|------|
| $C_{ies}$        | Input Capacitance                   | $V_{GE} = 0V$ $V_{CE} = 25V$   |  |     | 1100 |      |      |
| Coes             | Output Capacitance                  |  |  |     | 70   |      | pF   |
| C <sub>res</sub> | Reverse Transfer Capacitance        | f = 1MHz   |  | 35  |      |      |      |
| $Q_{G}$          | Gate charge                         | $V_{GE}=\pm 15V, I_{C}=2V_{CE}=300V$   |  | 0.2 |      | μС   |      |
| $T_{d(on)}$      | Turn-on Delay Time                  | Inductive Switch   |  | 110 |      |      |      |
| $T_{\rm r}$      | Rise Time                           | $V_{GE} = \pm 15V$   |  |     | 45   |      |      |
| $T_{d(off)}$     | Turn-off Delay Time                 | $I_{\rm Bus} = 300 \text{ V}$<br>$I_{\rm C} = 20 \text{ A}$  | $V_{\text{Bus}} = 300V$ $I_{\text{a}} = 20 \Delta$ |     | 200  |      | ns   |
| $T_{\mathrm{f}}$ | Fall Time                           | $R_G = 12\Omega$   |  | 40  |      |      |      |
| $T_{d(on)}$      | Turn-on Delay Time                  | Inductive Switch   |  | 120 |      | ns   |      |
| T <sub>r</sub>   | Rise Time                           | $\begin{aligned} V_{GE} &= \pm 15V \\ V_{Bus} &= 300V \\ I_{C} &= 20A \\ R_{G} &= 12\Omega \end{aligned}$  |  |     | 50   |      |      |
| $T_{d(off)}$     | Turn-off Delay Time                 |  |  |     | 250  |      |      |
| $T_{\rm f}$      | Fall Time                           |  |  |     | 60   |      |      |
| Eon              | Turn-on Switching Energy            | $ \begin{array}{lll} V_{GE} = \pm 15 V & T_{j} = 25^{\circ} C \\ V_{Bus} = 300 V & T_{j} = 150^{\circ} C \\ I_{C} = 20 A & T_{j} = 25^{\circ} C \\ R_{G} = 12 \Omega & T_{j} = 150^{\circ} C \end{array} $ | $T_j = 25$ °C                                      |     | 0.11 |      | mJ   |
| Lon              |                                     |  |  | 0.2 |      | 1113 |      |
| $E_{off}$        | Turn-off Switching Energy           |  |  |     | 0.5  |      | mJ   |
| -0II             | Tain on Switching Energy            |  | $K_G = 12\Omega$ $T_j = 150^{\circ}C$              |     | 0.7  |      | 1110 |
| $I_{sc}$         | Short Circuit data                  | $V_{GE} \le 15V ; V_{Bus} = 360V$<br>$t_p \le 6\mu s ; T_i = 150^{\circ}C$   |  |     | 100  |      | A    |
| $R_{thJC}$       | Junction to Case Thermal Resistance |  |  |     |      | 2.4  | °C/W |



## CR1 to CR6 diode ratings and characteristics

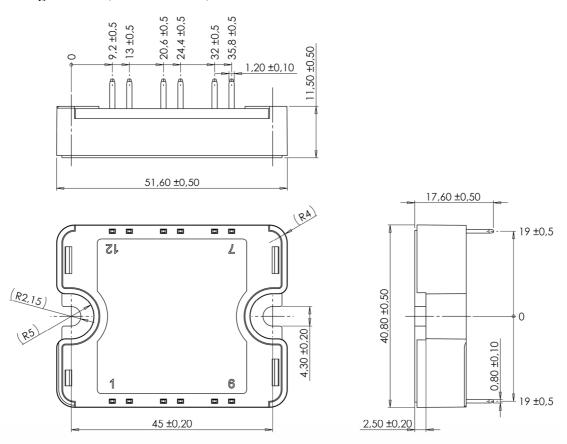
| Symbol           | Characteristic                          | Test Conditions                                |   | Min | Typ  | Max        | Unit |
|------------------|---|--|---|-----|------|------------|------|
| $V_{RRM}$        | Maximum Peak Repetitive Reverse Voltage |  |   | 600 |      |            | V    |
| $I_{RM}$         | Maximum Reverse Leakage Current         | V <sub>R</sub> =600V                           | $T_i = 25^{\circ}C$<br>$T_i = 150^{\circ}C$         |     |      | 150<br>350 | μA   |
| $I_{F}$          | DC Forward Current                      |  | $T_i = 130 \text{ C}$<br>$T_c = 80^{\circ}\text{C}$ |     | 20   | 330        | A    |
| V                | Diode Forward Voltage                   | $I_F = 20A$                                    | $T_i = 25^{\circ}C$                                 |     | 1.6  | 2          | V    |
| $V_{\mathrm{F}}$ |   | $V_{GE} = 0V$                                  | $T_{i} = 150^{\circ}C$                              |     | 1.5  |            | ·    |
| $t_{rr}$         | Reverse Recovery Time                   | $I_F = 20A$ $V_R = 300V$ $di/dt = 1600A/\mu s$ | $T_j = 25$ °C                                       |     | 100  |            | ns   |
| ٩rr              |   |  | $T_{j} = 150^{\circ}C$                              |     | 150  |            |      |
| Q <sub>rr</sub>  | Reverse Recovery Charge                 |  | $T_j = 25$ °C                                       |     | 1.1  |            | μС   |
| Vrr              |   |  | $T_{i} = 150^{\circ}C$                              |     | 2.3  |            | μС   |
| E <sub>rr</sub>  | Reverse Recovery Energy                 | and Tooorn as                                  | $T_j = 25$ °C                                       |     | 0.23 |            | mJ   |
| L <sub>II</sub>  |   |  | $T_j = 150$ °C                                      |     | 0.50 |            | 1113 |
| $R_{thJC}$       | Junction to Case Thermal Resistance     |  |   |     |      | 3.25       | °C/W |

## Thermal and package characteristics

| Symbol      | Characteristic   |             |    | Min  | Тур | Max | Unit |
|-------------|--|-------------|----|------|-----|-----|------|
| $V_{ISOL}$  | RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz |             |    | 4000 |     |     | V    |
| $T_{J}$     | Operating junction temperature range                           |             |    | -40  |     | 175 |      |
| $T_{STG}$   | Storage Temperature Range                                      |             |    | -40  |     | 125 | °C   |
| $T_{\rm C}$ | Operating Case Temperature                                     |             |    | -40  |     | 100 |      |
| Torque      | Mounting torque  | To heatsink | M4 | 2    |     | 3   | N.m  |
| Wt          | Package Weight   |             |    |      |     | 110 | g    |



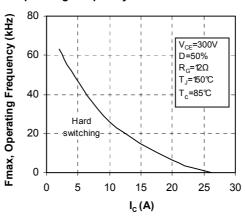
## SP1 Package outline (dimensions in mm)



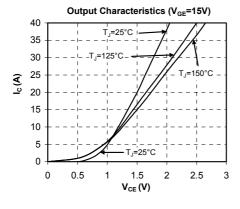
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

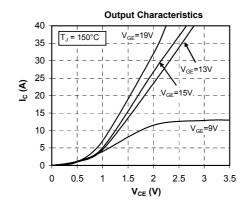
## Q1 to Q4 Typical performance curve

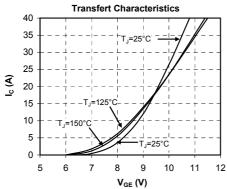
### **Operating Frequency vs Collector Current**

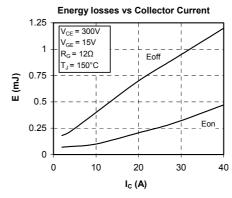


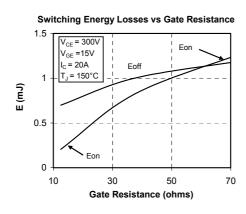


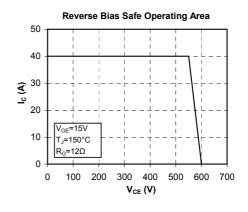


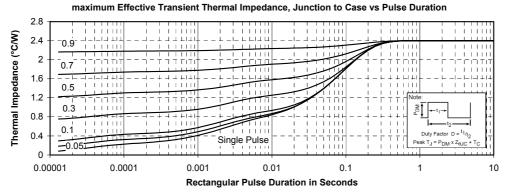






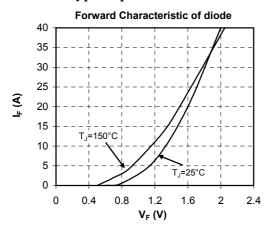




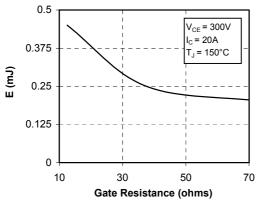




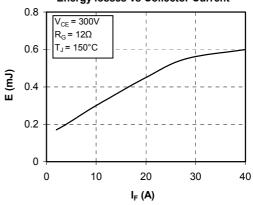
## CR1 to CR6 Typical performance curve



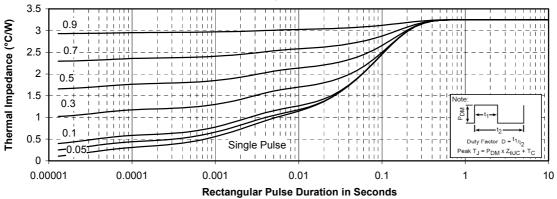
### **Switching Energy Losses vs Gate Resistance**



### **Energy losses vs Collector Current**



### maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration





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